

# SILICIDE RESISTOR IN BEOL LAYER OF SEMICONDUCTOR DEVICE AND METHOD

## Abstract

A silicide resistor for inclusion in a BEOL layer, and a method of forming the same that provides few additional manufacturing steps. The method allows formation of a passive resistor during BEOL processing without high temperature anneals that would damage other BEOL wiring structures. In particular, the method includes forming a silicide over a polysilicon base in a trough, where the silicide provides the desired resistivity and has a silicidation temperature less than a damaging temperature of the plurality of BEOL layers.